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(54) **POWER AMPLIFIER**

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(57) **ABSTRACT**

A power amplifier includes: a power transistor to receive a power voltage; a first transistor including a first terminal to provide a bias current to the power transistor; and an overpower protection circuit to generate a first current corresponding to the power voltage and to provide the first current to a second terminal of the first transistor. The overpower protection circuit includes: a limiting current source to provide a limiting current to the second terminal of the first transistor; and a sink current generating circuit including a second transistor that includes a control terminal to which a voltage corresponding to the power voltage is applied and a first terminal connected to the second terminal of the first transistor, and to sink a second current from the limiting current.

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